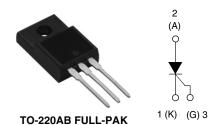




Vishay High Power Products

#### Phase Control SCR TO-220AB FULL-PAK, 16 A



PRODUCT SUMMARY				
V <sub>T</sub> at 10 A	1.4 V			
I <sub>TSM</sub>	200 A			
V <sub>RRM</sub>	800/1200 V			

#### **DESCRIPTION/FEATURES**

The 16TTS..FP High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

Typical applications are in input rectification (soft start) and these products are designed to be used with Vishay HPP input diodes, switches and output rectifiers which are available in identical package outlines.

Fully isolated package ( $V_{INS}$  = 2500  $V_{RMS}$ ) is UL E78996 approved

This product has been designed and qualified for industrial level.

OUTPUT CURRENT IN TYPICAL APPLICATIONS				
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS	
Capacitive input filter T <sub>A</sub> = 55 °C, T <sub>J</sub> = 125 °C, common heatsink of 1 °C/W	13.5	17	А	

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I <sub>T(AV)</sub>	Sinusoidal waveform	10	А		
I <sub>RMS</sub>		16	^		
V <sub>DRM</sub> /V <sub>RRM</sub>		800/1200	V		
I <sub>TSM</sub>		200	A		
V <sub>T</sub>	10 A, T <sub>J</sub> = 25 °C	1.4	V		
dV/dt		500	V/µs		
dl/dt		150	A/μs		
T <sub>J</sub>	Range	- 40 to 125	°C		

VOLTAGE RATINGS						
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA			
16TTS08FP	800	10				
16TTS12FP	1200	1200	10			

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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL		TEST CONDITIONS		VALUES	
PARAMETER	SYMBOL				MAX.	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	$I_{T(AV)}$ $T_c = 95$ °C, 180° conduction, half sine wave		1	0	
Maximum RMS on-state current	I <sub>RMS</sub>				6	
Maximum peak, one-cycle,	_	10 ms sine p	oulse, rated V <sub>RRM</sub> applied	1	70	Α
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine p	oulse, no voltage reapplied	2	00	
Marrian and 12th for fraction	l <sup>2</sup> t	10 ms sine p	oulse, rated V <sub>RRM</sub> applied	144		- A <sup>2</sup> s
Maximum I <sup>2</sup> t for fusing	I <sup>-</sup> t	10 ms sine p	10 ms sine pulse, no voltage reapplied		200	
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 to 10	t = 0.1 to 10 ms, no voltage reapplied		000	A²√s
Maximum on-state voltage drop	$V_{TM}$	10 A, T <sub>J</sub> = 25 °C		1	.4	٧
On-state slope resistance	r <sub>t</sub>	T 405 00		24	4.0	mΩ
Threshold voltage	V <sub>T(TO)</sub>	T <sub>J</sub> = 125 °C		1	.1	٧
Mariana		T <sub>J</sub> = 25 °C	V Batadiy Av	0	.5	
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	$V_R = Rated V_{RRM}/V_{DRM}$		0	
Holding current	I <sub>H</sub>		ly = 6 V, resistive load, initial I <sub>T</sub> = 1 A , 16TTS12FP	-	100	mA
Maximum latching current	ΙL	Anode supply = 6 V, resistive load		2	00	
Maximum rate of rise of off-state voltage	dV/dt			5	00	V/µs
Maximum rate of rise of turned-on current	dl/dt			1	50	A/μs

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	$P_{GM}$		8.0	w
Maximum average gate power	P <sub>G(AV)</sub>		2.0	]
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	90	mA
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	60	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	35	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	3.0	
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	V
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	]
Maximum DC gate voltage not to trigger	$V_{GD}$	$T_{J} = 125 ^{\circ}\text{C},  V_{DRM} = \text{Rated value}$ $0.2$ $2.0$		
Maximum DC gate current not to trigger	I <sub>GD</sub>			mA

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9		
Typical reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C	4	μs	
Typical turn-off time	tq	1J = 125 C	110		



# Phase Control SCR Vishay High Power Products TO-220AB FULL-PAK, 16 A

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		$T_J$ , $T_{Stg}$		- 40 to 125	°C
Maximum thermal resistance, junction to case		$R_{\text{thJC}}$	DC operation	1.5	
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		62	°C/W
Typical thermal resistance, case to heatsink		$R_{thCS}$	Mounting surface, smooth and greased	1.5	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mounting torque ————	minimum			6 (5)	kgf · cm
	maximum			12 (10)	(lbf · in)
Marking device			Consiste TO COOME FULL DAY (04A/O)	16TTS08FP	
			Case style TO-220AB FULL-PAK (94/V0)	16TTS12FP	

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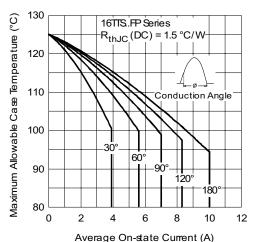
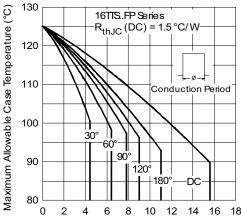


Fig. 1 - Current Rating Characteristics



Average On-state Current (A)
Fig. 2 - Current Rating Characteristics

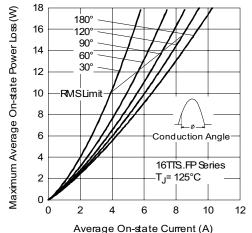


Fig. 3 - On-State Power Loss Characteristics

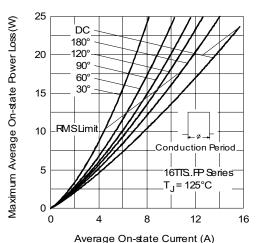
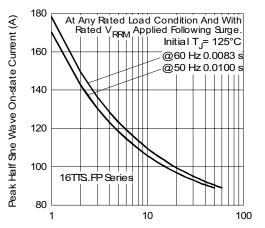


Fig. 4 - On-State Power Loss Characteristics



 $\label{eq:number of Equal Amplitude Half Cycle Current Pulses (N)} Number of Equal Amplitude Half Cycle Current Pulses (N)$ 

Fig. 5 - Maximum Non-Repetitive Surge Current

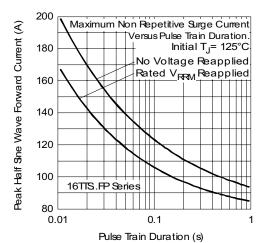


Fig. 6 - Maximum Non-Repetitive Surge Current



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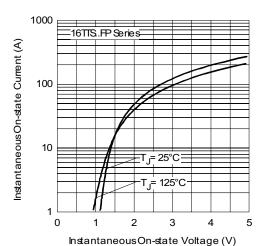
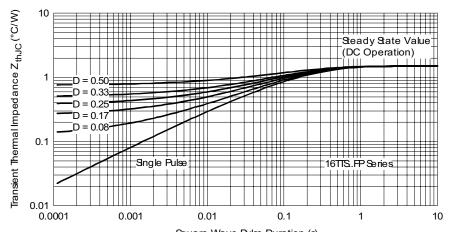
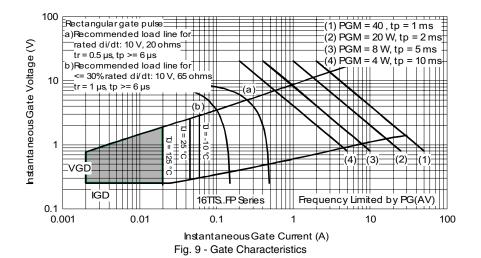


Fig. 7 - On-State Voltage Drop Characteristics



 $\label{eq:square Wave Pulse Duration (s)} \mbox{Fig. 8 - Thermal impedance $Z_{thJC}$ Characteristics}$ 



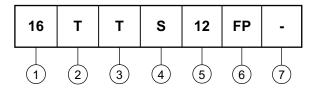
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Phase Control SCR TO-220AB FULL-PAK, 16 A



#### **ORDERING INFORMATION TABLE**

Device code



- 1 Current rating, RMS value
- 2 Circuit configuration:

T = Single thyristor

Package:

T = TO-220AB

4 - Type of silicon:

S = Converter grade

5 - Voltage code x 100 = V<sub>RRM</sub> - 08 = 800 V 12 = 1200 V

6 - FULL-PAK

7 - • None = Standard production

• PbF = Lead (Pb)-free

Note: For higher voltage up to 1600 V contact factory

LINKS TO RELATED DOCUMENTS				
Dimensions http://www.vishay.com/doc?95072				
Part marking information	http://www.vishay.com/doc?95069			



Vishay

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